

Edition 1.0 2021-04

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Integrated circuits TEMC evaluation of transceivers FIFW Part 5: Ethernet transceivers (standards.iteh.ai)

<u>IEC 62228-5:2021</u> https://standards.iteh.ai/catalog/standards/sist/70278798-8a4c-4822-8c35-1f14f02d2f9f/iec-62228-5-2021





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INTERNATIONAL ELECTROTECHNICAL COMMISSION

ICS 31.200 ISBN 978-2-8322-9697-4

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# INTEGRATED CIRCUITS – EMC EVALUATION OF TRANSCEIVERS –

## Part 5: Ethernet transceivers

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International Standard IEC 62228-5 has been prepared by subcommittee 47A: Integrated circuits, of IEC technical committee 47: Semiconductor devices.

The text of this International Standard is based on the following documents:

Draft	Report on voting
47A/1115/FDIS	47A/1117/RVD

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at www.iec.ch/members\_experts/refdocs. The main document types developed by IEC are described in greater detail at www.iec.ch/standardsdev/publications.

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# **INTEGRATED CIRCUITS -EMC EVALUATION OF TRANSCEIVERS -**

# Part 5: Ethernet transceivers

# Scope

This part of IEC 62228 specifies test and measurement methods for EMC evaluation of Ethernet transceiver ICs under network condition. It defines test configurations, test conditions, test signals, failure criteria, test procedures, test setups and test boards. It is applicable for transceiver of the Ethernet systems

- 100BASE-T1 according to ISO/IEC/IEEE 8802-3/AMD1;
- 100BASE-TX according to ISO/IEC/IEEE 8802-3;
- 1000BASE-T1 according to ISO/IEC/IEEE 8802-3/AMD4

#### and covers

- the emission of RF disturbances;
- the immunity against RF disturbances; ) A RD PREVIEW
- the immunity against impulses;

amendments) applies.

andards.iteh.ai) the immunity against electrostatic discharges (ESD)

# IEC 62228-5:2021

1f14f02d2f9f/iec-62228-5-2021 The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any

IEC 61967-1, Integrated circuits – Measurement of electromagnetic emissions – Part 1: General conditions and definitions

IEC 61967-4, Integrated circuits - Measurement of electromagnetic emissions, 150 kHz to 1 GHz - Part 4: Measurement of conducted emissions, 1 ohm/150 ohm direct coupling method

IEC 62132-1, Integrated circuits – Measurement of electromagnetic immunity – Part 1: General conditions and definitions

IEC 62132-4, Integrated circuits - Measurement of electromagnetic immunity 150 kHz to 1 GHz - Part 4: Direct RF power injection method

IEC 62215-3, Integrated circuits - Measurement of impulse immunity - Part 3: Nonsynchronous transient injection method

IEC 62228-1, Integrated circuits – EMC evaluation of transceivers – Part 1: General conditions and definitions

ISO 10605, Road vehicles - Test methods for electrical disturbances from electrostatic discharge

ISO 21111-2, Road vehicles – In-vehicle Ethernet – Part 2: Common physical entity requirements

ISO 7637-2, Road vehicles – Electrical disturbances from conduction and coupling – Part 2: Electrical transient conduction along supply lines only

ISO/IEC/IEEE 8802-3:2017, Information technology – Telecommunications and information exchange between systems – Local and metropolitan area networks – Specific requirements – Part 3: Standard for Ethernet

ISO/IEC/IEEE 8802-3:2017/AMD1:2017, Amendment 1 – Information technology – Telecommunications and information exchange between systems – Local and metropolitan area networks – Specific requirements – Part 3: Standard for Ethernet – Physical layer specifications and management parameters for 100 Mb/s operation over a single balanced twisted pair cable (100BASE-T1)

ISO/IEC/IEEE 8802-3:2017/AMD4:2017, Amendment 4 – Information technology – Telecommunications and information exchange between systems – Local and metropolitan area networks – Specific requirements – Part 3: Standard for Ethernet – Physical layer specifications and management parameters for 1 Gb/s operation over a single twisted-pair copper cable

Electronic Components Industry Association, EIA-198-1, *Ceramic Dielectric Capacitors Classes I, II, III and IV* 

# iTeh STANDARD PREVIEW

# 3 Terms, definitions and abbreviated terms (standards.iteh.ai)

For the purposes of this document, the terms and definitions given in IEC 61967-1, IEC 62132-1, IEC 62228-1, as well as the following apply 62228-5:2021

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ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- ISO Online browsing platform: available at http://www.iso.org/obp
- IEC Electropedia: available at http://www.electropedia.org/

## 3.1 Terms and definitions

## 3.1.1

# 100BASE-T1 transceiver

transceiver 100 Mbit/s via single balanced twisted pair, with a functionality according to ISO/IEC/IEEE 8802-3/AMD1 (100BASE-T1)

## 3.1.2

# 100BASE-TX transceiver

transceiver 100 Mbit/s via two balanced twisted pairs, with a functionality according to ISO/IEC/IEEE 8802-3(100BASE-TX)

# 3.1.3

# 1000BASE-T1 transceiver

transceiver 1000 Mbit/s via single balanced twisted pair, with a functionality according to ISO/IEC/IEEE 8802-3/AMD4 (1000BASE-T1)

# 3.1.4

## global pin

pin that carries a signal or power, which enters or leaves the application board without any active component in between

#### 3.1.5

# local pin

pin that carries a signal or power, which does not leave the application board

#### 3.1.6

# mandatory components

pΙ

components needed for proper function and/or technical requirement of IC as specified by the IC manufacturer

## 3.1.7

# switch

IC with integrated Ethernet transceivers and switch functionality as defined in ISO/IEC/IEEE 8802-3

#### 3.2 Abbreviated terms

**ASIC** Application specific integrated circuit

BIN Bus interface network

BIST Built in self-test

CMC Common mode choke

CDMR Common to differential mode conversion ratio

CMR Common mode rejection

Differential to common mode conversion ratio DCMR

Direct RF power injection ards.iteh.ai) DPI

DTT Data transfer test

IEC 62228-5:2021

Device under test https://standards.iteh.ai/catalog/standards/sist/70278798-8a4c-4822-8c35-DUT

**FPGA** Field programmable gate array-62228-5-2021

GMII Gigabit media independent interface **GPIO** General purpose input or output

IL Insertion loss

INH Inhibit

LCL Longitudinal conversion loss

LPF Low pass filter

MDI Medium dependent interface MII Media independent interface

PCB Printed circuit board

PRBS Pseudo random bit stream PHY Ethernet single transceiver

RGMII Reduced gigabit media independent interface

RL Return loss

RS-FEC Reed Solomon forward error correction

SBC System base chip

SGMII Serial gigabit media independent interface

SNR Signal-to-noise ratio S-parameter Scattering parameter SQI Signal quality indicator TDR Time domain reflectometry TLP Transmission line pulse VNA Vector network analyzer

#### General

The intention of this document is to evaluate the EMC performance of Ethernet transceivers under application conditions in a minimal network.

The evaluation of the EMC characteristics of Ethernet transceivers shall be performed for the implemented functional operation modes as defined in Table 1 under network condition for conducted RF emission and RF immunity tests and impulse immunity tests and on a single transceiver IC for electrostatic discharge tests.

The aim of these tests is to determine the EMC performance on dedicated pins of the Ethernet transceiver which are considered as EMC relevant in the application. For an Ethernet transceiver, these pins are global pins like MDIP, MDIN,  $V_{\mathsf{BAT}}$  and WAKE as well as local pins like power supply inputs  $(V_{\text{DDx}})$ . The global pin WAKE is given as an example and represents any global pin other than MDI and voltage supply  $V_{BAT}$ .

If the DUT includes additional product specific EMC relevant pins (functions), it shall be tested as well. The test conditions and failure validation criteria shall be adapted to the definitions for the standard functionality of Ethernet transceivers.

The test methods used for the EMC characterization are based on the international standards for IC EMC tests and are described in Table 1.

https/Table 1 - Overview of measurements and tests 35-

Configuration	Test	Test method	Evaluation	Functional operation mode
	RF conducted emission (EMI)	150 Ω direct coupling (IEC 61967-4)	Spectrum	Normal
	RF conducted	DPI (IEC 62132-4)		Normal
Transceiver network	immunity (RF)		Function	Low power
Transceiver network	Impulse immunity	Non-synchronous transient injection (IEC 62215-3)	Function	Normal
	(IMP)			Low power
	ESD noward	red Contact discharge (ISO 10605)	Function	Normal
	ESD powered			Low power
Single transceiver	ESD unpowered	Contact discharge (ISO 10605)	Damage	Unpowered

The 150  $\Omega$  direct coupling, DPI and impulse immunity test methods are chosen for the evaluation of the conducted EMC characteristic of transceivers in network condition. These three test methods are based on the same approach using conductive coupling. Therefore, it is possible to use the same test board for all tests in functional operation mode, which reduces the effort and increases the reproducibility and comparability of test results.

Powered ESD test will be performed using the same approach of testing the Ethernet transceiver under network conditions but a modified test board is used because of RF and ESD tests cannot be combined on one test board if all specific test conditions of each test method should be covered.